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Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S1	10	(("6514830") or ("6350639") or ("6025240") or ("6187644") or ("6294432")).PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/10/13 17:37
S2	6	("3673679"   "4470191"   "4830974"   "5296401"   "5427971"   "6191044").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/10/13 14:09
S3	1	("6350639").URPN.	USPAT	OR	ON	2005/10/13 14:09
S4	6	("3673679"   "4470191"   "4830974"   "5296401"   "5427971"   "6191044").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/10/13 14:08
S5	7	("3673679"   "4470191"   "4830974"   "5296401"   "5427971"   "6191044").PN. OR ("6350639"). URPN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/10/13 14:08
S6	4	("4558338"   "5834817"   "5937299"   "6013570").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/10/13 14:12
S7	1293	(438/301).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/10/13 16:23
S8	415	S7 and (ldd (lightly adj doped adj (source drain)))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/13 17:38
S9	0	("2005/0202642").URPN.	USPAT	OR	ON	2005/10/13 17:35
S10	651	(438/302).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR .	OFF · "	2005/10/13 17:37
S11	270	S10 and (ldd (lightly adj doped adj (source drain)))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/14 13:39

S12	4893	((438/301) or (438/302) or (438/303) or (438/304) or (438/305) or (438/306) or (438/307)).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/10/16 17:56
S13	2179	S12 and (Idd (lightly adj doped adj (source drain)))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/14 13:39
S14	2147	S13 and ((ion impurit\$3 atom) nera4 implant\$4)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/14 13:41
S15	641	S14 and (rie (react\$4 adj ion adj etch\$3))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/16 18:35
S16	74	S15 and (mosfet and nmos and pmos)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON .	2005/10/14 13:45
S17	0	S15 and (Cl and HBr and O and CF and He)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/16 18:36
S18	2	S15 and (Cl and HBr)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/14 13:55
S19	289	S15 and ((lpcvd (low adj pressure adj chemical adj vapor adj deposit\$3)) pecvd)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/14 14:02

636	204	C15 and //lagred //arrea #1	HC DCDHD	00	ON	2005/10/14 14 02
S20	294	S15 and ((Ipcvd (low adj pressure adj chemical adj vapor adj deposit\$3)) pecvd (plasma adj enhanced adj chemical adj vapor adj deposit\$3))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/14 14:03
S21	65	S20 and ((arsine phosphine) and (silane disilane))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/14 14:04
S22	0	("2005/0095799").URPN.	USPAT	OR	ON	2005/10/14 14:15
S23	_ 5	S21 and ((SiN (silicon adj nitride)) and (SiNO (silicon adj oxynitride)) and (SiO (silicon adj oxide)))	USPAT	OR	ON	2005/10/14 14:18
S24	.4893	((438/301) or (438/302) or (438/303) or (438/304) or (438/305) or (438/306) or (438/307)).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/10/16 17:57
S25	1377	S24 and ((pattern\$3 shap\$3) near3 (mask\$3 resit\$3))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/16 17:58
S26	3850	S24 and ((remov\$3 delet\$3) nera3 (pattern\$3 shap\$3) near3 (mask\$3 resit\$3))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/16 18:00
S27	154	S24 and ((remov\$3 delet\$3) near3 (pattern\$3 shap\$3) near3 (mask\$3 resit\$3))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/16 18:00
S28	19	S27 and (hot near3 (phosphor\$3 adj acid))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/16 18:01
S29	1044	S24 and (rie (react\$4 adj ion adj etch\$3))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/16 18:46

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S30		S29 and (Cl and HBr and O and CF and He and N)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/16 18:38
<b>S31</b>	0	S29 and (Cl and HBr and CF)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/16 18:37
S32	0	S29 and (HBr and CF)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/16 18:37
S33	1	S29 and (Chlori\$3 and HBr and oxid\$3 and (carbon adj tetrafluoride) and helium and nitrid\$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/16 18:47
S34	87671	mosfet (metal adj oxide adj semiconductor adj field adj effect adj transistor)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/16 18:45
S35	5539	S34 and (rie (react\$4 adj ion adj etch\$3))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR .	ON	2005/10/16 18:46
S36	2	S35 and (Chlori\$3 and HBr and oxid\$3 and (carbon adj tetrafluoride) and helium and nitrid\$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/16 18:47